

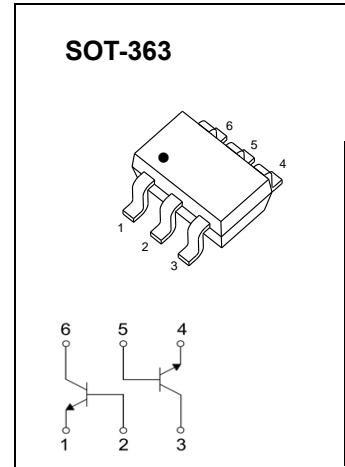
MMDT3904 DUAL TRANSISTOR(NPN+NPN)

FEATURES

- Epitaxial planar die construction
- Ideal for low power amplification and switching

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5	V
I _c	Collector Current -Continuous	0.2	A
P _c	Collector Power Dissipation	0.2	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =10µA,I _e =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c =1mA,I _b =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _e =10µA,I _c =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =30V,I _e =0			0.05	µA
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _c =0			0.05	µA
Collector cut-off current	I _{CEX}	V _{CE} =30V,V _{BE(off)} =3V			0.05	µA
DC current gain	h _{FE(1)}	V _{CE} =1V,I _c =0.1mA	40			
	h _{FE(2)}	V _{CE} =1V,I _c =1mA	70			
	h _{FE(3)}	V _{CE} =1V,I _c =10mA	100		300	
	h _{FE(4)}	V _{CE} =1V,I _c =50mA	60			
	h _{FE(5)}	V _{CE} =1V,I _c =100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _c =10mA,I _b =1mA			0.2	V
	V _{CE(sat)2}	I _c =50mA,I _b =5mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _c =10mA,I _b =1mA	0.65		0.85	V
	V _{BE(sat)2}	I _c =50mA,I _b =5mA			0.95	V
Transition frequency	f _T	V _{CE} =20V,I _c =10mA,f=100MHz	300			MHz
Collector output capacitance	C _{ob}	V _{CB} =5V,I _e =0,f=1MHz			4	pF
Noise figure	NF	V _{CE} =5V,I _c =0.1mA,f=1kHz,R _s =1KΩ			5	dB
Delay time	t _d	V _{CC} =3V,V _{BE(off)} =-0.5V I _c =10mA, I _{b1} =-I _{b2} = 1mA			35	nS
Rise time	t _r				35	nS
Storage time	t _s	V _{CC} =3V, I _c =10mA I _{b1} =-I _{b2} =1mA			200	nS
Fall time	t _f				50	nS

Typical Characteristics

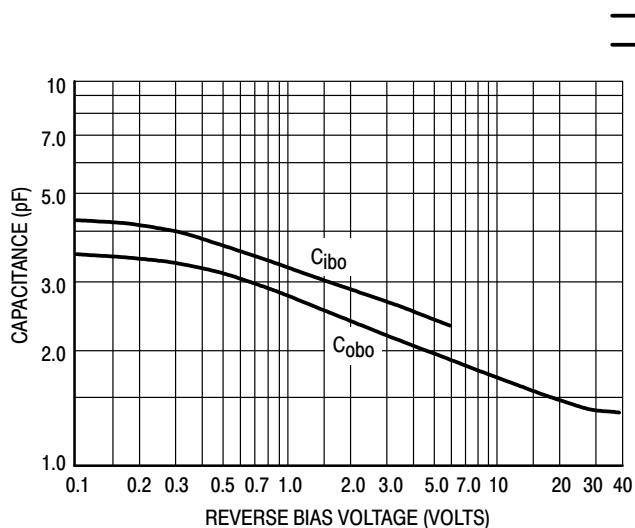


Figure 3. Capacitance

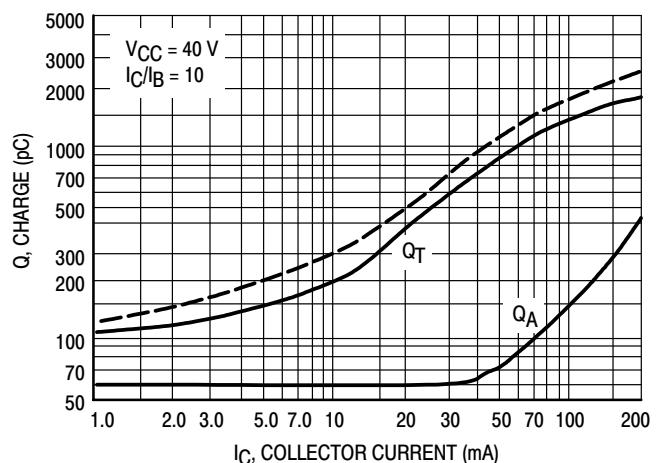


Figure 4. Charge Data

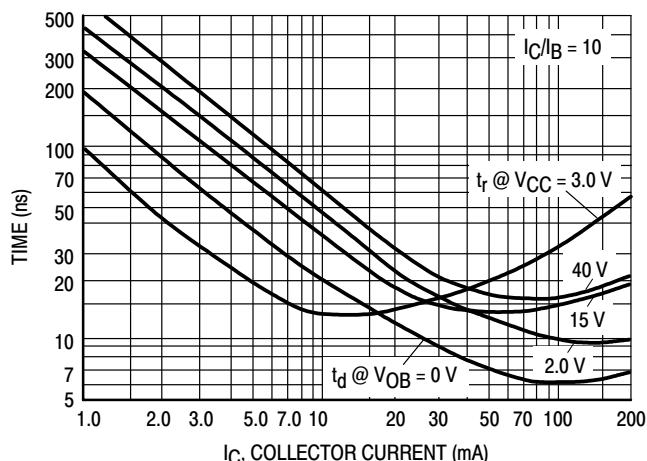


Figure 5. Turn-On Time

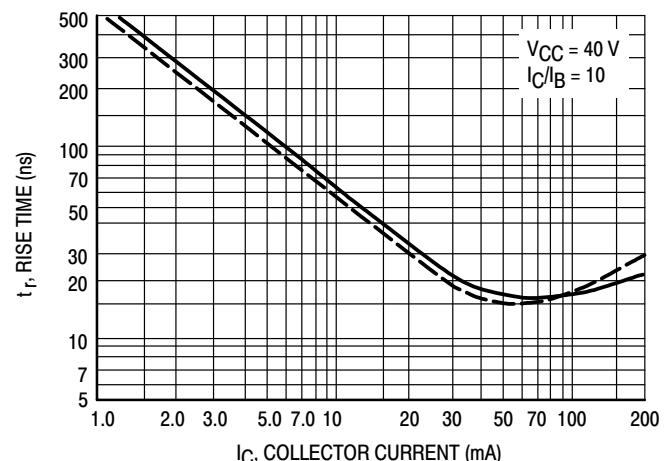


Figure 6. Rise Time

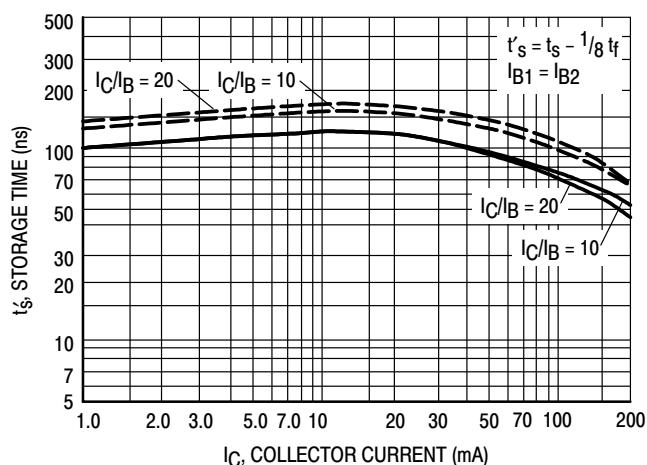


Figure 7. Storage Time

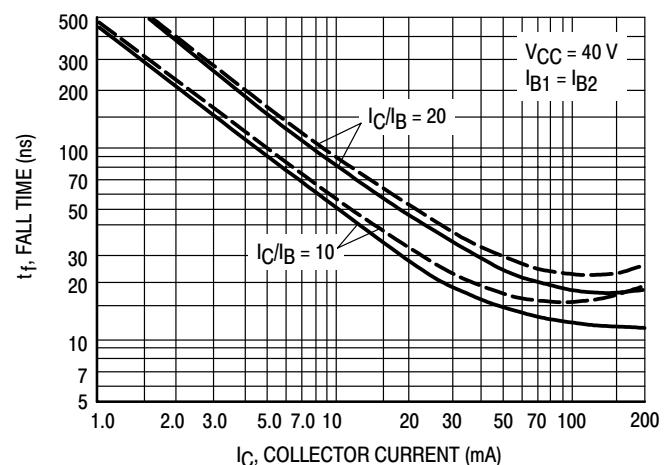
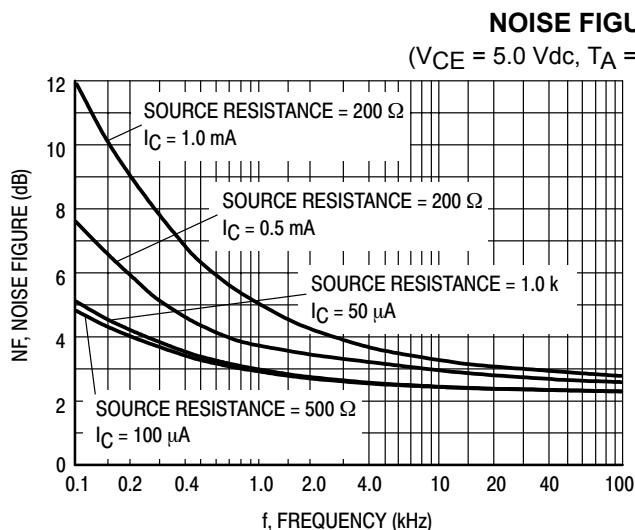
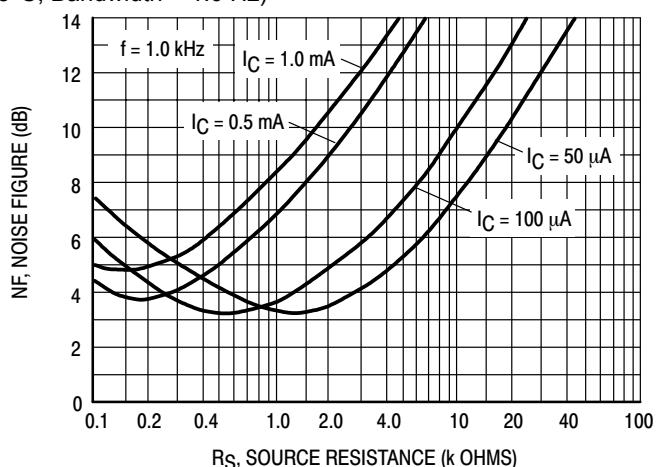
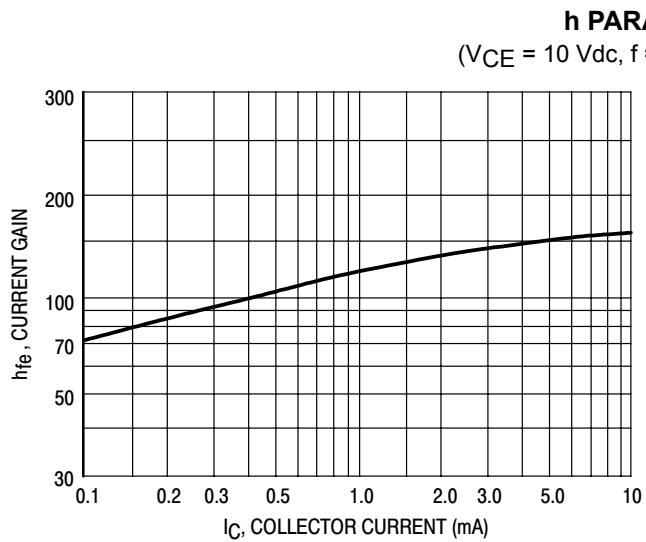
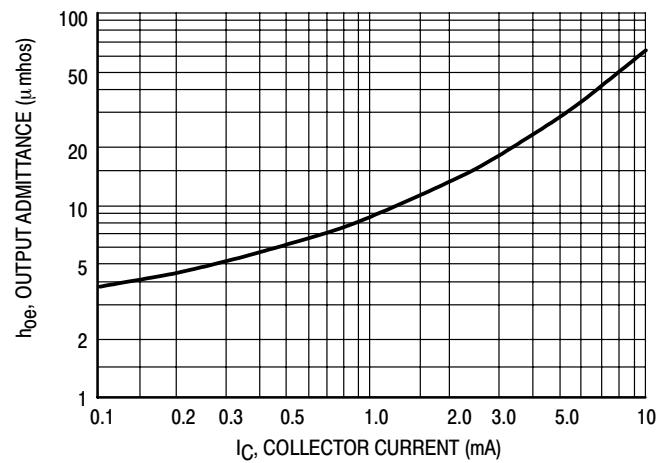
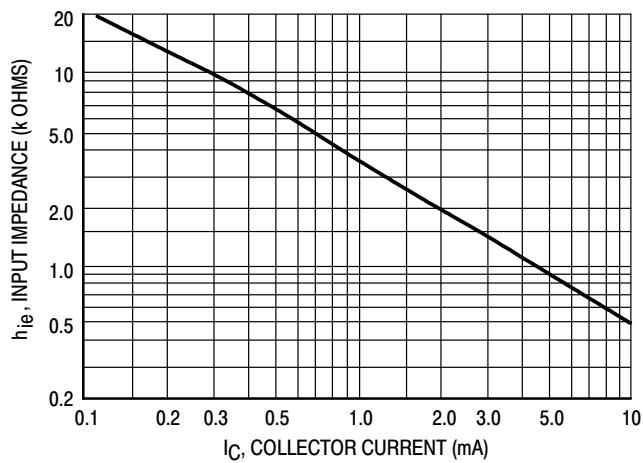
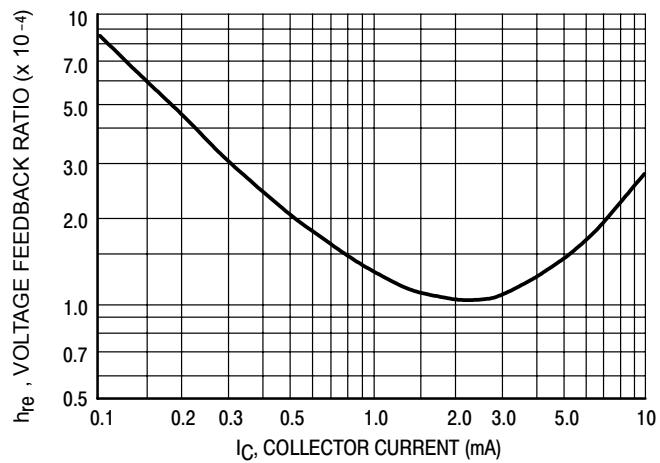
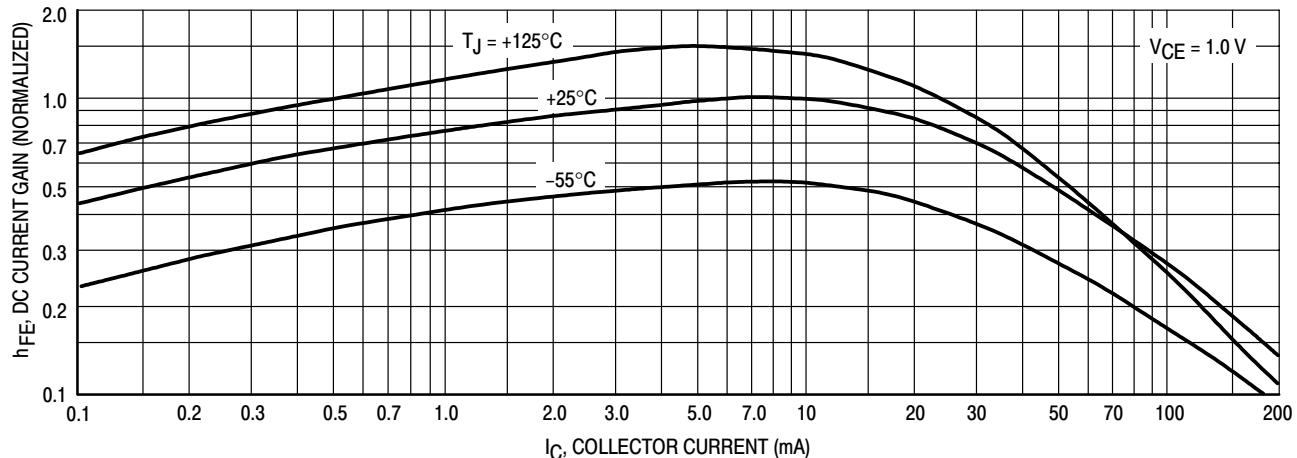
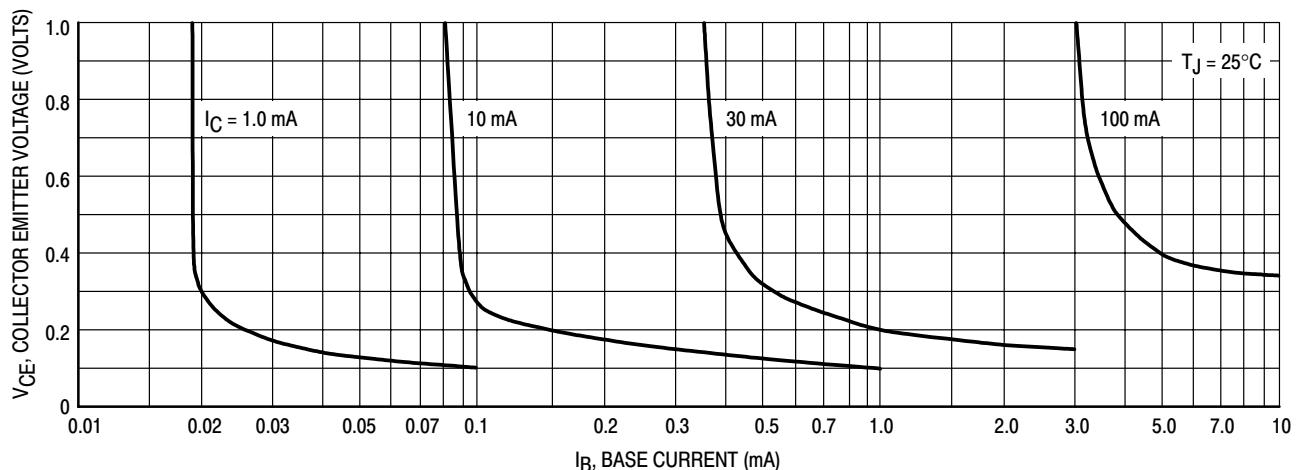
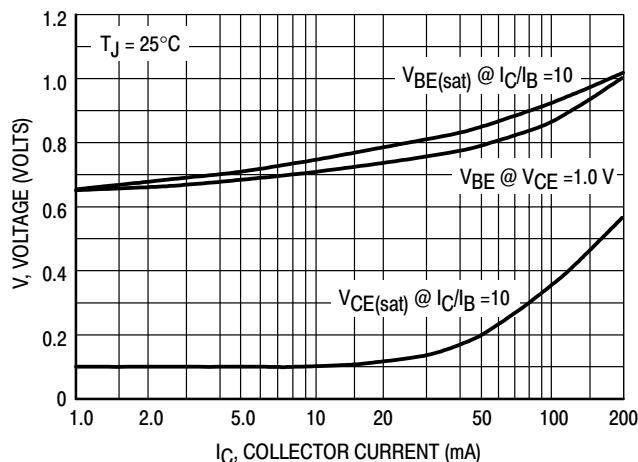
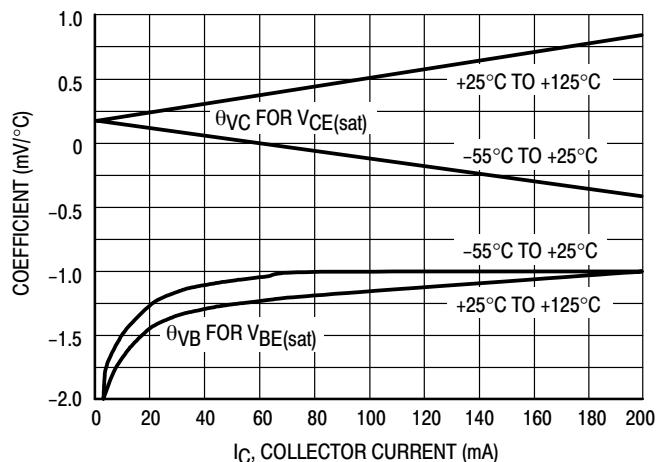


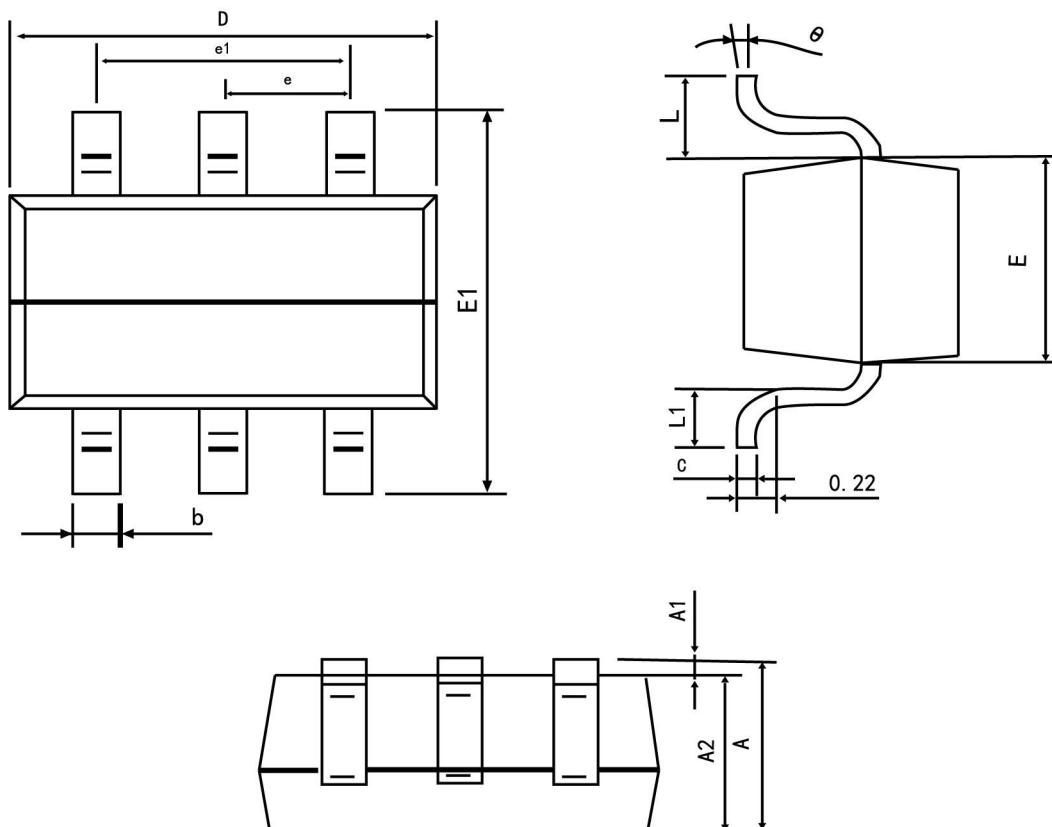
Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS

Figure 9. Noise Figure

Figure 10. Noise Figure

Figure 11. Current Gain

Figure 12. Output Admittance

Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

Figure 15. DC Current Gain

Figure 16. Collector Saturation Region

Figure 17. "ON" Voltages

Figure 18. Temperature Coefficients

Package Outline Dimensions

SOT-363



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°

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